

TABLE 1. PIN DESCRIPTIONS

Name	Type	Description
XTAL_OUT	Output	Crystal oscillator interface. XTAL_OUT is the output.
XTAL_IN	Input	Crystal oscillator interface. XTAL_IN is the input.
ENABLE 1, ENABLE 2	Input	Clock enable. LVCMOS / LVTTL interface levels. See Table 3.
BCLK0, BCLK1, BCLK2, BCLK3, BCLK4, BCLK5	Output	Clock outputs. LVCMOS / LVTTL interface levels.
GND	Power	Power supply ground.
V _{DD}	Power	Core supply pin.
V _{DDO}	Power	Output supply pin.
n/c	Unused	No connect.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
C _{PD}	Power Dissipation Capacitance (per output)	V _{DDO} = 3.465V			19	pF
		V _{DDO} = 2.625V			18	pF
		V _{DDO} = 2V			16	pF
R _{OUT}	Output Impedance	V _{DDO} = 3.3V ± 5%		7		Ω
		V _{DDO} = 2.5V ± 5%		7		Ω
		V _{DDO} = 1.8V ± 0.2V		10		Ω

TABLE 3. CLOCK ENABLE FUNCTION TABLE

Control Inputs		Outputs	
ENABLE 1	ENABLE 2	BCLK0:BCLK4	BCLK5
0	0	LOW	LOW
0	1	LOW	Toggling
1	0	Toggling	LOW
1	1	Toggling	Toggling

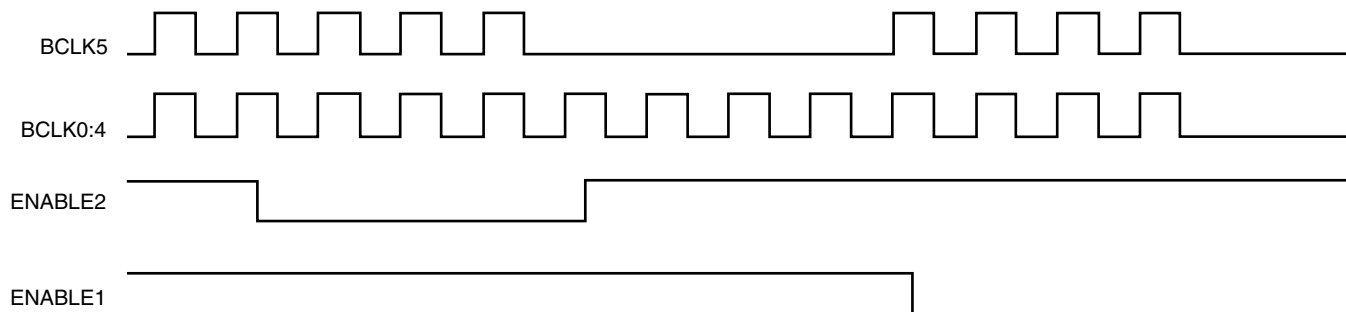


FIGURE 1. ENABLE TIMING DIAGRAM

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to $V_{DD} + 0.5V$
Outputs, V_O	-0.5V to $V_{DDO} + 0.5V$
Package Thermal Impedance, θ_{JA}	
16 Lead SOIC package	78.8°C/W (0 mps)
16 Lead TSSOP package	89°C/W (0 lfpn)
20 Lead VFQFN package	60.4°C/W (0 mps)
Storage Temperature, T_{STG}	-65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

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TABLE 4A. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = 0^\circ\text{C}$ TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Core Supply Voltage		3.135	3.3	3.465	V
V_{DDO}	Output Supply Voltage		3.135	3.3	3.465	V
I_{DD}	Power Supply Current	ENABLE 1:2 = 00			10	mA
I_{DDO}	Output Supply Current	ENABLE 1:2 = 00			5	mA

TABLE 4B. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = V_{DDO} = 2.5V \pm 5\%$, $T_A = 0^\circ\text{C}$ TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Core Supply Voltage		2.375	2.5	2.625	V
V_{DDO}	Output Supply Voltage		2.375	2.5	2.625	V
I_{DD}	Power Supply Current	ENABLE 1:2 = 00			8	mA
I_{DDO}	Output Supply Current	ENABLE 1:2 = 00			4	mA

TABLE 4C. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = V_{DDO} = 1.8V \pm 0.2V$, $T_A = 0^\circ\text{C}$ TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Core Supply Voltage		1.6	1.8	2.0	V
V_{DDO}	Output Supply Voltage		1.6	1.8	2.0	V
I_{DD}	Power Supply Current	ENABLE 1:2 = 00			5	mA
I_{DDO}	Output Supply Current	ENABLE 1:2 = 00			3	mA

TABLE 4D. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, $T_A = 0^\circ\text{C}$ TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Core Supply Voltage		3.135	3.3	3.465	V
V_{DDO}	Output Supply Voltage		2.375	2.5	2.625	V
I_{DD}	Power Supply Current	ENABLE 1:2 = 00			10	mA
I_{DDO}	Output Supply Current	ENABLE 1:2 = 00			4	mA

TABLE 4E. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 1.8V \pm 0.2V$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Core Supply Voltage		3.135	3.3	3.465	V
V_{DDO}	Output Supply Voltage		1.6	1.8	2.0	V
I_{DD}	Power Supply Current	ENABLE 1:2 = 00			10	mA
I_{DDO}	Output Supply Current	ENABLE 1:2 = 00			3	mA

TABLE 4F. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = 2.5V \pm 5\%$, $V_{DDO} = 1.8V \pm 0.2V$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Core Supply Voltage		2.375	2.5	2.625	V
V_{DDO}	Output Supply Voltage		1.6	1.8	2.0	V
I_{DD}	Power Supply Current	ENABLE 1:2 = 00			8	mA
I_{DDO}	Output Supply Current	ENABLE 1:2 = 00			3	mA

TABLE 4G. LVCMOS/LVTTL DC CHARACTERISTICS, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage	ENABLE 1, ENABLE 2	$V_{DD} = 3.3V \pm 5\%$	2	$V_{DD} + 0.3$	V
			$V_{DD} = 2.5V \pm 5\%$	1.7	$V_{DD} + 0.3$	V
			$V_{DD} = 1.8V \pm 0.2V$	$0.65 \cdot V_{DD}$	$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage	ENABLE 1, ENABLE 2	$V_{DD} = 3.3V \pm 5\%$	-0.3	0.8	V
			$V_{DD} = 2.5V \pm 5\%$	-0.3	0.7	V
			$V_{DD} = 1.8V \pm 0.2V$	-0.3	$0.35 \cdot V_{DD}$	V
V_{OH}	Output High Voltage	$V_{DDO} = 3.3V \pm 5\%$; NOTE 1	2.6			V
		$V_{DDO} = 2.5V \pm 5\%$; $I_{OH} = -1mA$	2			V
		$V_{DDO} = 2.5V \pm 5\%$; NOTE 1	1.8			V
		$V_{DDO} = 1.8V \pm 0.2V$; NOTE 1	$V_{DDO} - 0.3$			V
V_{OL}	Output Low Voltage	$V_{DDO} = 3.3V \pm 5\%$; NOTE 1			0.5	V
		$V_{DDO} = 2.5V \pm 5\%$; $I_{OL} = 1mA$			0.4	V
		$V_{DDO} = 2.5V \pm 5\%$; NOTE 1			0.45	V
		$V_{DDO} = 1.8V \pm 0.2V$; NOTE 1			0.35	V

NOTE 1: Outputs terminated with 50Ω to $V_{DDO}/2$. See Parameter Measurement section, "Load Test Circuit" diagrams.

TABLE 5. CRYSTAL CHARACTERISTICS

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fundamental			
Frequency		10		40	MHz
Equivalent Series Resistance (ESR)				50	Ω
Shunt Capacitance				7	pF
Drive Level				1	mW

TABLE 6A. AC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency	Using External Crystal		10		40	MHz
		Using External Clock Source; NOTE 1		DC		100	MHz
odc	Output Duty Cycle			48		52	%
$t_{sk(o)}$	Output Skew; NOTE 2, 4					80	ps
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random)		25MHz @ (Integration Range: 100Hz-1MHz)		0.13		ps
t_R/t_F	Output Rise/Fall Time		20% to 80%	200		800	ps
t_{EN}	Output Enable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles
t_{DIS}	Output Disable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles

All parameters measured at $f \leq f_{MAX}$ using a crystal input unless noted otherwise.

Terminated at 50Ω to $V_{DDO}/2$.

NOTE 1: XTAL_IN can be overdriven relative to a signal a crystal would provide.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

NOTE 3: These parameters are guaranteed by characterization. Not tested in production.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

TABLE 6B. AC CHARACTERISTICS, $V_{DD} = V_{DDO} = 2.5V \pm 5\%$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency	Using External Crystal		10		40	MHz
		Using External Clock Source; NOTE 1		DC		100	MHz
odc	Output Duty Cycle			47		53	%
$t_{sk(o)}$	Output Skew; NOTE 2, 5					80	ps
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random); NOTE 3		25MHz @ (Integration Range: 100Hz-1MHz)		0.26		ps
t_R/t_F	Output Rise/Fall Time		20% to 80%	200		800	ps
t_{EN}	Output Enable Time; NOTE 4	ENABLE 1				4	cycles
		ENABLE 2				4	cycles
t_{DIS}	Output Disable Time; NOTE 4	ENABLE 1				4	cycles
		ENABLE 2				4	cycles

All parameters measured at $f \leq f_{MAX}$ using a crystal input unless noted otherwise.

Terminated at 50Ω to $V_{DDO}/2$.

NOTE 1: XTAL_IN can be overdriven relative to a signal a crystal would provide.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

NOTE 3: Please refer to phase noise plot.

NOTE 4: These parameters are guaranteed by characterization. Not tested in production.

NOTE 5: This parameter is defined in accordance with JEDEC Standard 65.

TABLE 6C. AC CHARACTERISTICS, $V_{DD} = V_{DDO} = 1.8V \pm 0.2V$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency	Using External Crystal		10		40	MHz
		Using External Clock Source; NOTE 1		DC		100	MHz
odc	Output Duty Cycle			47		53	%
$tsk(o)$	Output Skew; NOTE 2, 4					80	ps
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random)		25MHz @ (Integration Range: 100Hz-1MHz)		0.27		ps
t_R/t_F	Output Rise/Fall Time		20% to 80%	200		900	ps
t_{EN}	Output Enable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles
t_{DIS}	Output Disable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles

All parameters measured at $f \leq f_{MAX}$ using a crystal input unless noted otherwise.

Terminated at 50Ω to $V_{DDO}/2$.

NOTE 1: XTAL_IN can be overdriven relative to a signal a crystal would provide.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

NOTE 3: These parameters are guaranteed by characterization. Not tested in production.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

TABLE 6D. AC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency	Using External Crystal		10		40	MHz
		Using External Clock Source; NOTE 1		DC		100	MHz
odc	Output Duty Cycle			48		52	%
$tsk(o)$	Output Skew; NOTE 2, 4					80	ps
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random)		25MHz @ (Integration Range: 100Hz-1MHz)		0.14		ps
t_R/t_F	Output Rise/Fall Time		20% to 80%	200		800	ps
t_{EN}	Output Enable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles
t_{DIS}	Output Disable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles

All parameters measured at $f \leq f_{MAX}$ using a crystal input unless noted otherwise.

Terminated at 50Ω to $V_{DDO}/2$.

NOTE 1: XTAL_IN can be overdriven relative to a signal a crystal would provide.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

NOTE 3: These parameters are guaranteed by characterization. Not tested in production.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

TABLE 6E. AC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 1.8V \pm 0.2V$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency	Using External Crystal		10		40	MHz
		Using External Clock Source; NOTE 1		DC		100	MHz
odc	Output Duty Cycle			48		52	%
$tsk(o)$	Output Skew; NOTE 2, 4					80	ps
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random)		25MHz @ (Integration Range: 100Hz-1MHz)		0.18		ps
t_R/t_F	Output Rise/Fall Time		20% to 80%	200		900	ps
t_{EN}	Output Enable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles
t_{DIS}	Output Disable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles

All parameters measured at $f \leq f_{MAX}$ using a crystal input unless noted otherwise.

Terminated at 50Ω to $V_{DDO}/2$.

NOTE 1: XTAL_IN can be overdriven relative to a signal a crystal would provide.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

NOTE 3: These parameters are guaranteed by characterization. Not tested in production.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

TABLE 6F. AC CHARACTERISTICS, $V_{DD} = 2.5V \pm 5\%$, $V_{DDO} = 1.8V \pm 0.2V$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency	Using External Crystal		10		40	MHz
		Using External Clock Source; NOTE 1		DC		100	MHz
odc	Output Duty Cycle			47		53	%
$tsk(o)$	Output Skew; NOTE 2, 4					80	ps
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random)		25MHz @ (Integration Range: 100Hz-1MHz)		0.19		ps
t_R/t_F	Output Rise/Fall Time		20% to 80%	200		900	ps
t_{EN}	Output Enable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles
t_{DIS}	Output Disable Time; NOTE 3	ENABLE 1				4	cycles
		ENABLE 2				4	cycles

All parameters measured at $f \leq f_{MAX}$ using a crystal input unless noted otherwise.

Terminated at 50Ω to $V_{DDO}/2$.

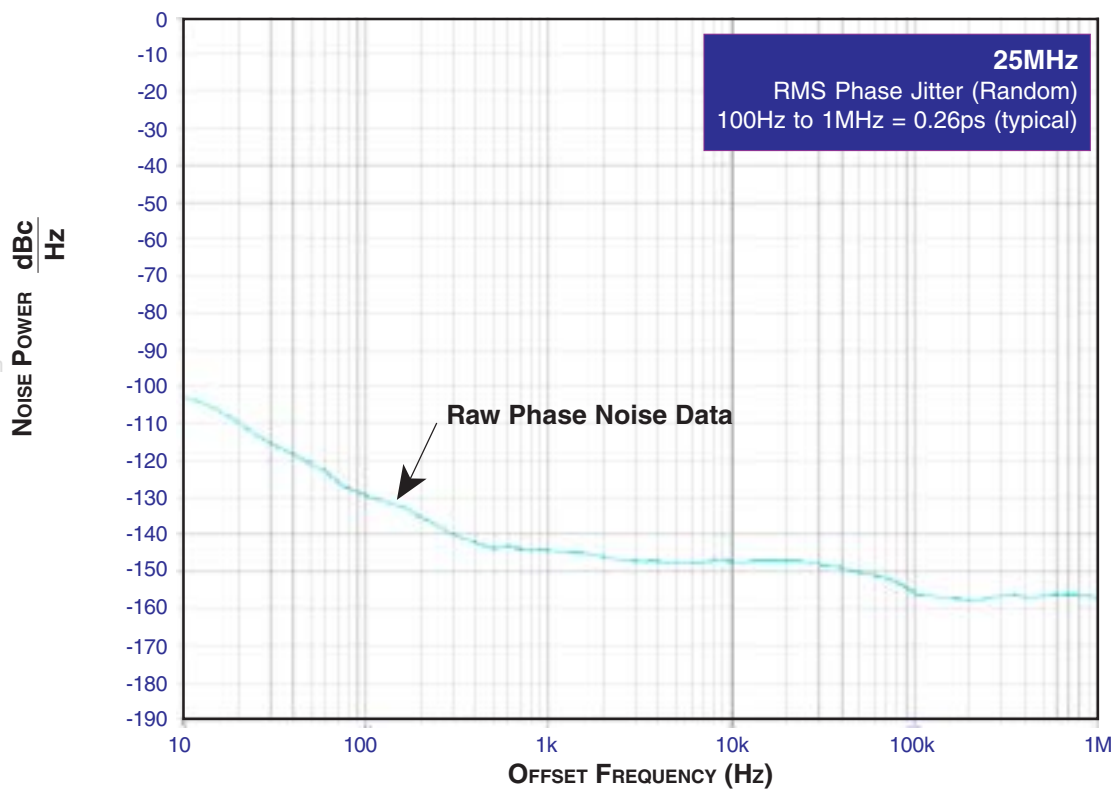
NOTE 1: XTAL_IN can be overdriven relative to a signal a crystal would provide.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

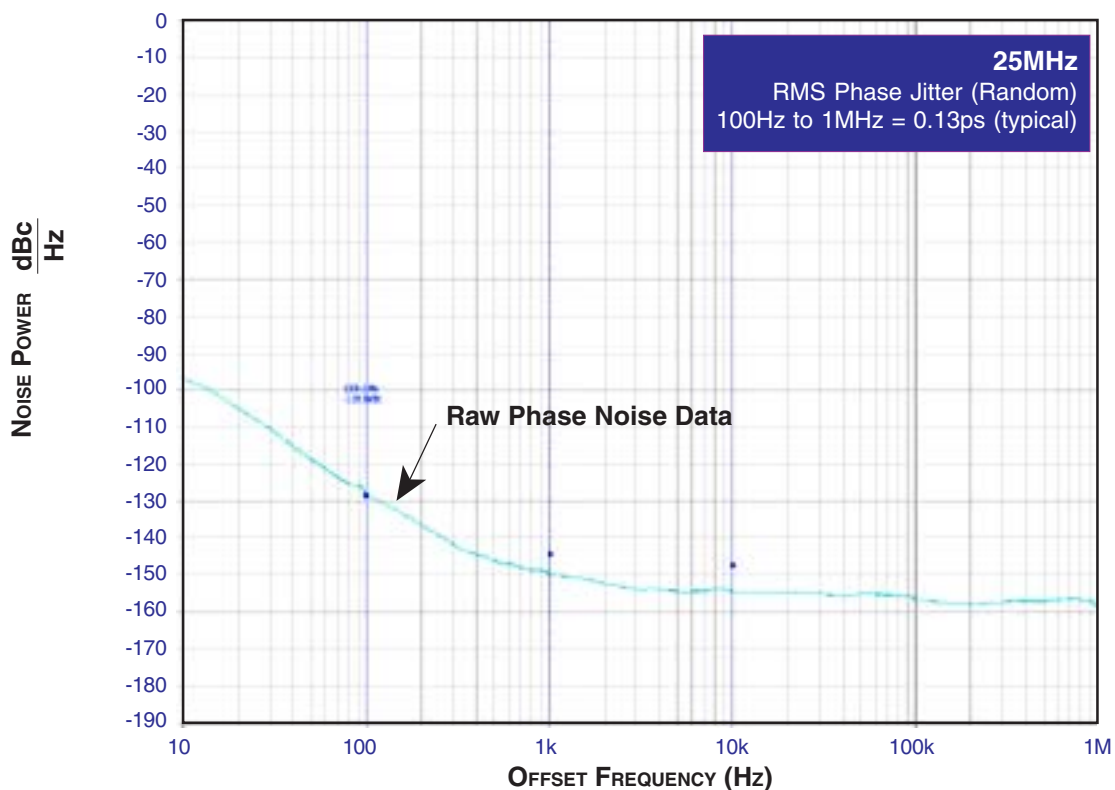
NOTE 3: These parameters are guaranteed by characterization. Not tested in production.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

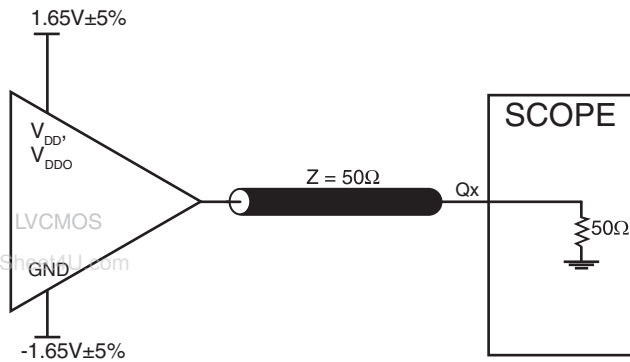
TYPICAL PHASE NOISE AT 25MHz (2.5V CORE/ 2.5V OUTPUT)



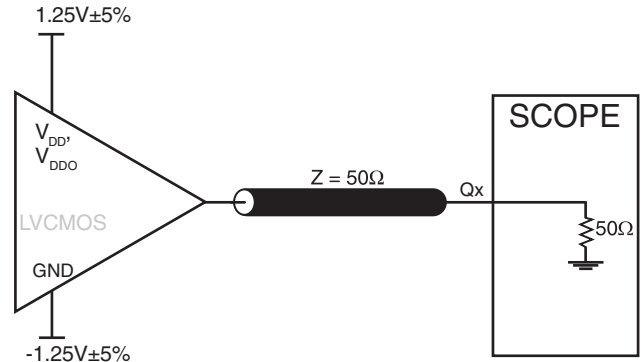
TYPICAL PHASE NOISE AT 25MHz (3.3V CORE/ 3.3V OUTPUT)



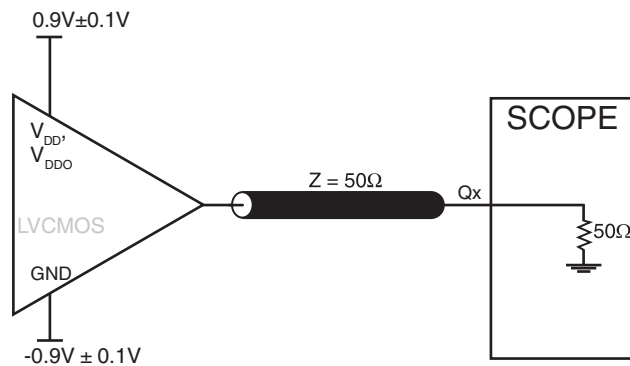
PARAMETER MEASUREMENT INFORMATION



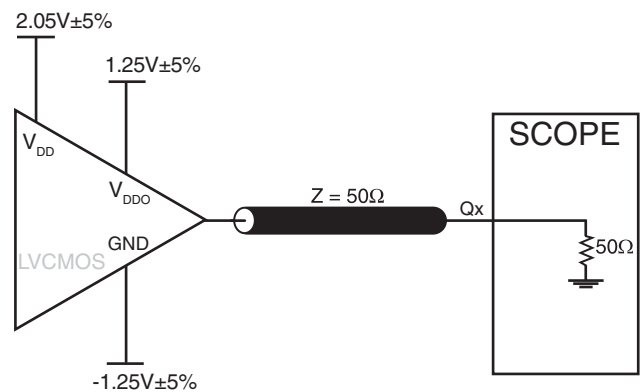
3.3V CORE/3.3V OUTPUT LOAD AC TEST CIRCUIT



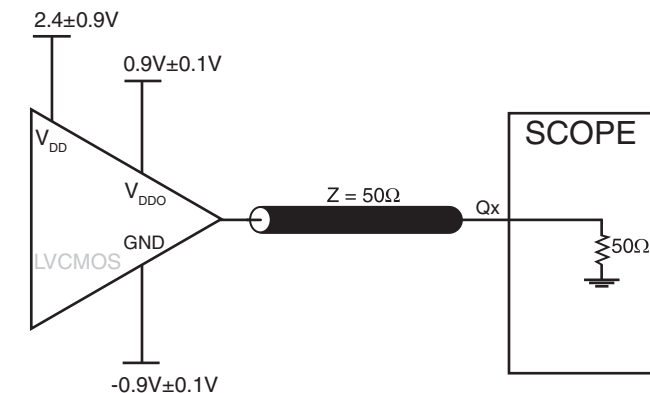
2.5V CORE/2.5V OUTPUT LOAD AC TEST CIRCUIT



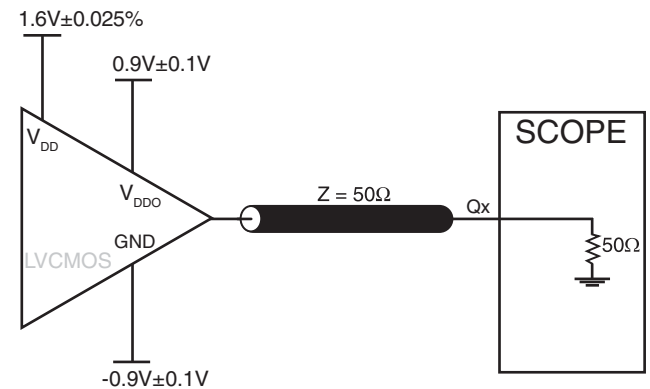
1.8V CORE/1.8V OUTPUT LOAD AC TEST CIRCUIT



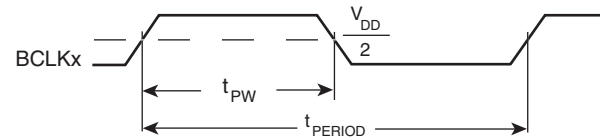
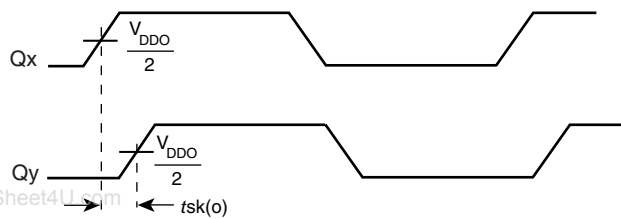
3.3V CORE/2.5V OUTPUT LOAD AC TEST CIRCUIT



3.3V CORE/1.8V OUTPUT LOAD AC TEST CIRCUIT



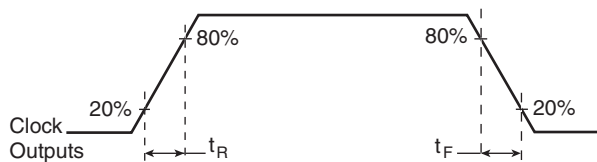
2.5 CORE/1.8V OUTPUT LOAD AC TEST CIRCUIT



$$odc = \frac{t_{PW}}{t_{PERIOD}} \times 100\%$$

OUTPUT SKEW

OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD



OUTPUT RISE/FALL TIME

APPLICATION INFORMATION

CRYSTAL INPUT INTERFACE

Figure 2 shows an example of ICS83905 crystal interface with a parallel resonant crystal. The frequency accuracy can be fine tuned by adjusting the C1 and C2 values. For a parallel crystal with loading capacitance $C_L = 18\text{pF}$, we suggest $C1 = 15\text{pF}$ and $C2 = 15\text{pF}$ to start with. These values may be slightly fine tuned further to optimize the frequency accuracy for different board

layouts. Slightly increasing the C1 and C2 values will slightly reduce the frequency. Slightly decreasing the C1 and C2 values will slightly increase the frequency. For the oscillator circuit below, R1 can be used, but is not required. For new designs, it is recommended that R1 not be used.

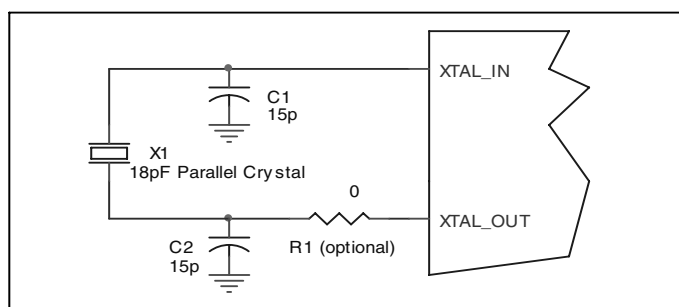


FIGURE 2. CRYSTAL OSCILLATOR INTERFACE

LVCMOS TO XTAL INTERFACE

The XTAL_IN input can accept a single-ended LVCMOS signal through an AC couple capacitor. A general interface diagram is shown in Figure 3. The XTAL_OUT pin can be left floating. The input edge rate can be as slow as 10ns. For LVCMOS inputs, it is recommended that the amplitude be reduced from full swing to half swing in order to prevent signal interference with the power rail and to reduce noise. This configuration requires that the output impedance of the driver

(R_o) plus the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First, R1 and R2 in parallel should equal the transmission line impedance. For most 50Ω applications, R1 and R2 can be 100Ω . This can also be accomplished by removing R1 and making R2 50Ω .

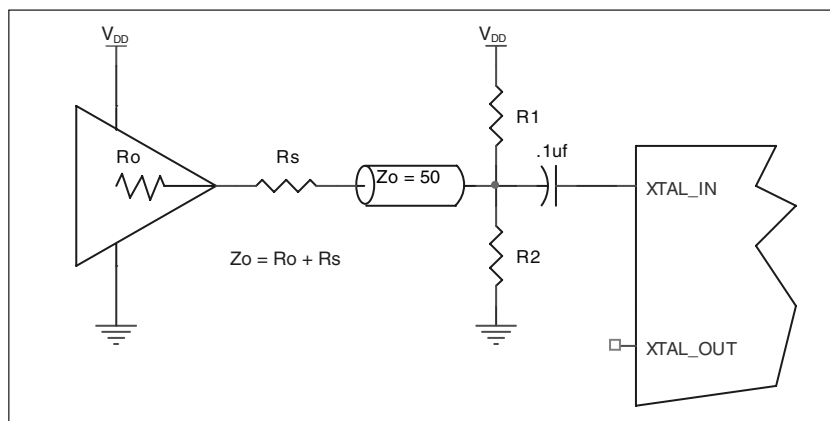


FIGURE 3. GENERAL DIAGRAM FOR LVCMOS DRIVER TO XTAL INPUT INTERFACE

RECOMMENDATIONS FOR UNUSED INPUT AND OUTPUT PINS

INPUTS:

LVCMOS CONTROL PINS

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

OUTPUTS:

LVCMOS OUTPUTS

All unused LVCMOS output can be left floating. There should be no trace attached.

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THERMAL RELEASE PATH

The expose metal pad provides heat transfer from the device to the P.C. board. The expose metal pad is ground pad connected to ground plane through thermal via. The exposed pad on the device to the exposed metal pad on the PCB is contacted through

solder as shown in *Figure 4*. For further information, please refer to the Application Note on Surface Mount Assembly of Amkor's Thermally /Electrically Enhance Leadframe Base Package, Amkor Technology.

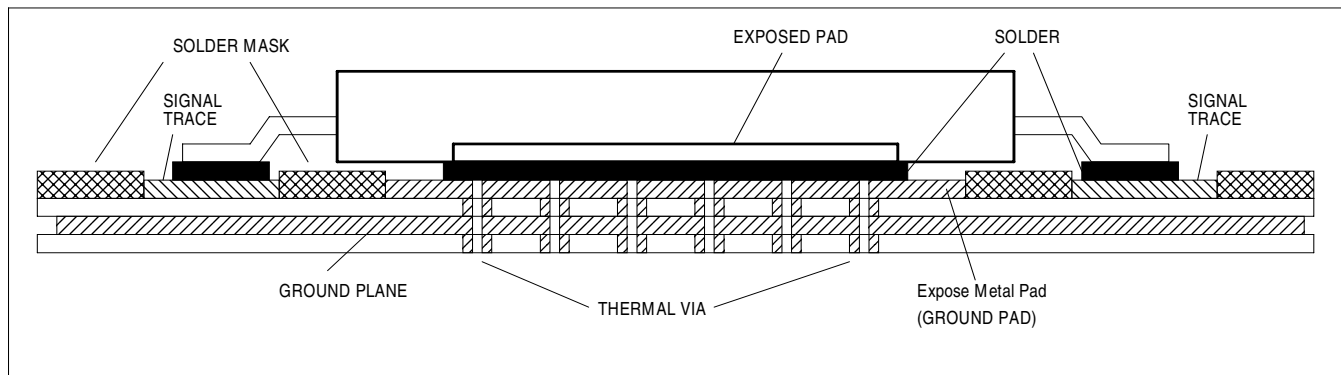


FIGURE 4. P.C. BOARD FOR EXPOSED PAD THERMAL RELEASE PATH EXAMPLE

LAYOUT GUIDELINE

Figure 5 shows an example of ICS83905 application schematic. In this example, the device is operated at $V_{DD} = 3.3V$ and $V_{DDO} = 3.3V$. The decoupling capacitors should be located as close as possible to the power pins. The input is driven by an 18pF load resonant quartz crystal. The tuning capacitors (C1, C2) are fairly

accurate, but minor adjustments might be required. For the LVCMOS output drivers, two termination examples are shown in the schematic. For additional termination, examples are shown in the LVCMOS Termination Application Note.

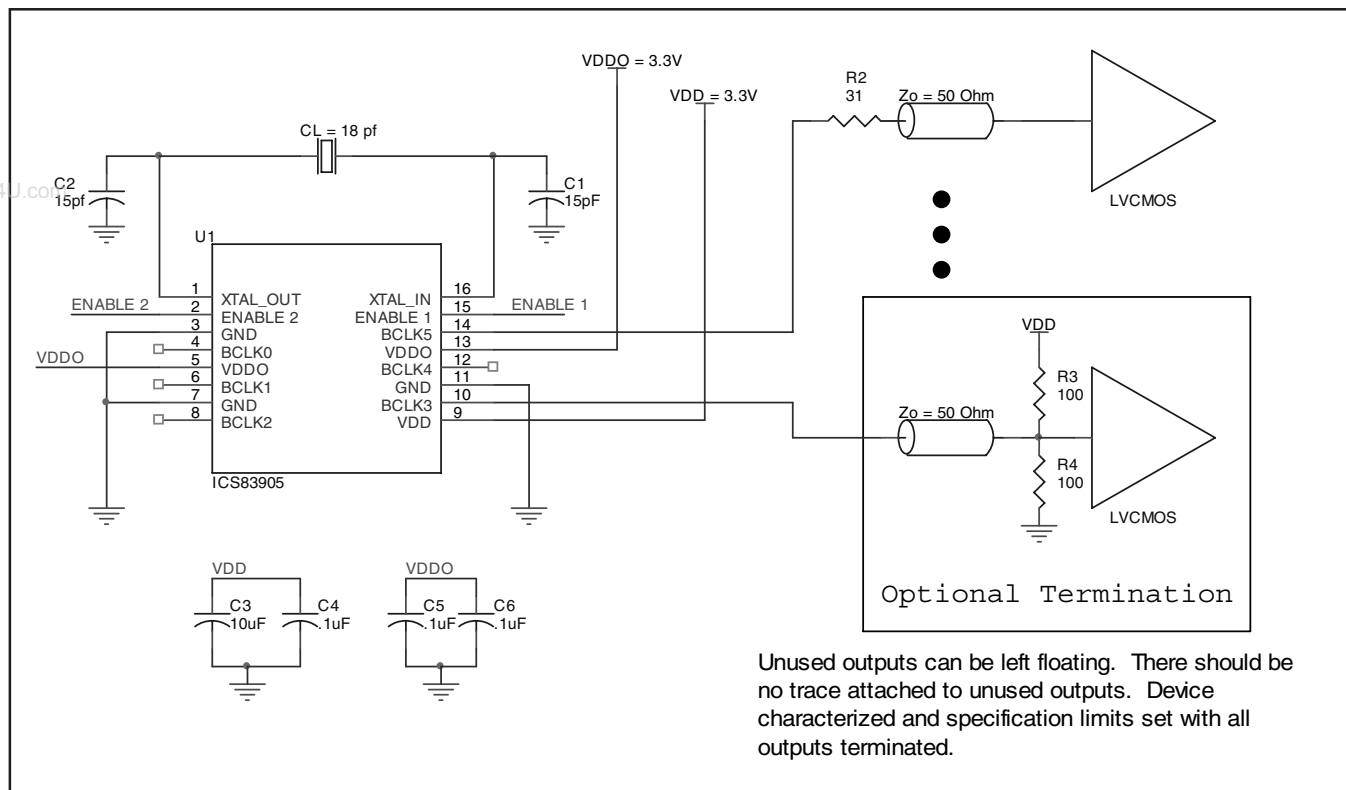


FIGURE 5. SCHEMATIC OF RECOMMENDED LAYOUT

RELIABILITY INFORMATION

TABLE 7A. θ_{JA} vs. AIR FLOW TABLE FOR 16 LEAD SOIC

θ_{JA} by Velocity (Meters per Second)			
	0	1	2
Multi-Layer PCB, JEDEC Standard Test Boards	78.8°C/W	71.1°C/W	66.2°C/W

TABLE 7B. θ_{JA} vs. AIR FLOW TABLE FOR 16 LEAD TSSOP

θ_{JA} by Velocity (Linear Feet per Minute)			
	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	137.1°C/W	118.2°C/W	106.8°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	89.0°C/W	81.8°C/W	78.1°C/W
NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.			

TABLE 7C. θ_{JA} vs. AIR FLOW TABLE FOR 20 LEAD VFQFN

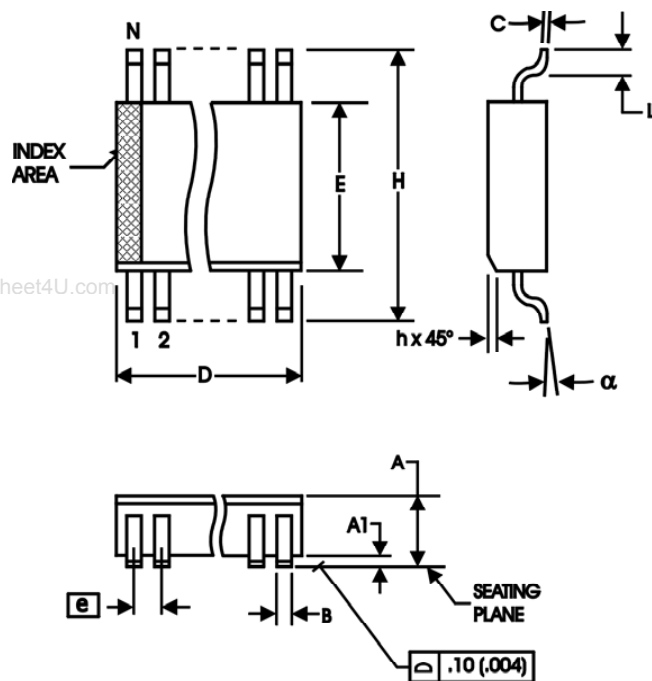
θ_{JA} by Velocity (Meters per Second)			
	0	1	3
Multi-Layer PCB, JEDEC Standard Test Boards	60.4°C/W	52.8°C/W	46.0°C/W

TRANSISTOR COUNT

The transistor count for ICS83905 is: 339

Pin compatible to MPC905

PACKAGE OUTLINE - M SUFFIX FOR 16 LEAD SOIC



PACKAGE OUTLINE - G SUFFIX FOR 16 LEAD TSSOP

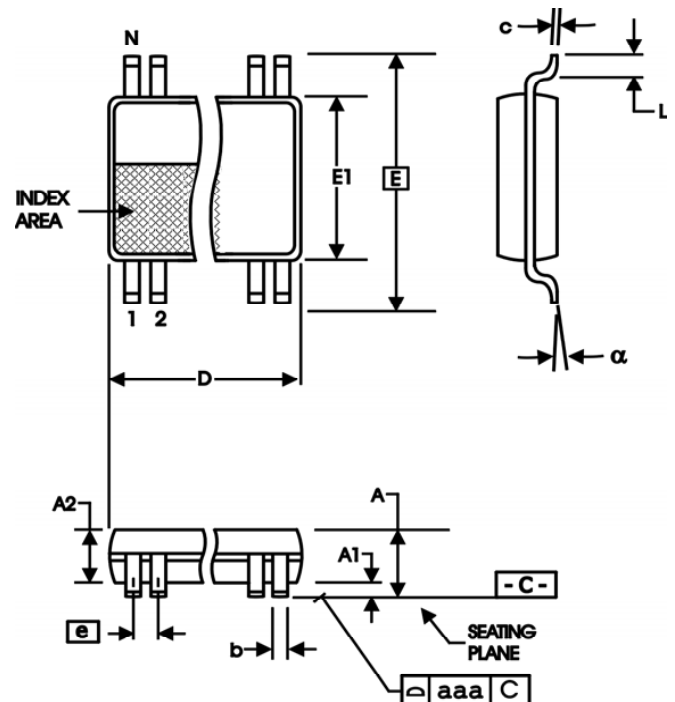


TABLE 8A. PACKAGE DIMENSIONS FOR 16 LEAD SOIC

SYMBOL	Millimeters	
	MINIMUM	MAXIMUM
N	16	
A	1.35	1.75
A1	0.10	0.25
B	0.33	0.51
C	0.19	0.25
D	9.80	10.00
E	3.80	4.00
e	1.27 BASIC	
H	5.80	6.20
h	0.25	0.50
L	0.40	1.27
α	0°	8°

Reference Document: JEDEC Publication 95, MS-012

TABLE 8B. PACKAGE DIMENSIONS FOR TSSOP

SYMBOL	Millimeters	
	Minimum	Maximum
N	16	
A	--	1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	4.90	5.10
E	6.40 BASIC	
E1	4.30	4.50
e	0.65 BASIC	
L	0.45	0.75
α	0°	8°
aaa	--	0.10

PACKAGE OUTLINE - K SUFFIX FOR 20 LEAD VFQFN

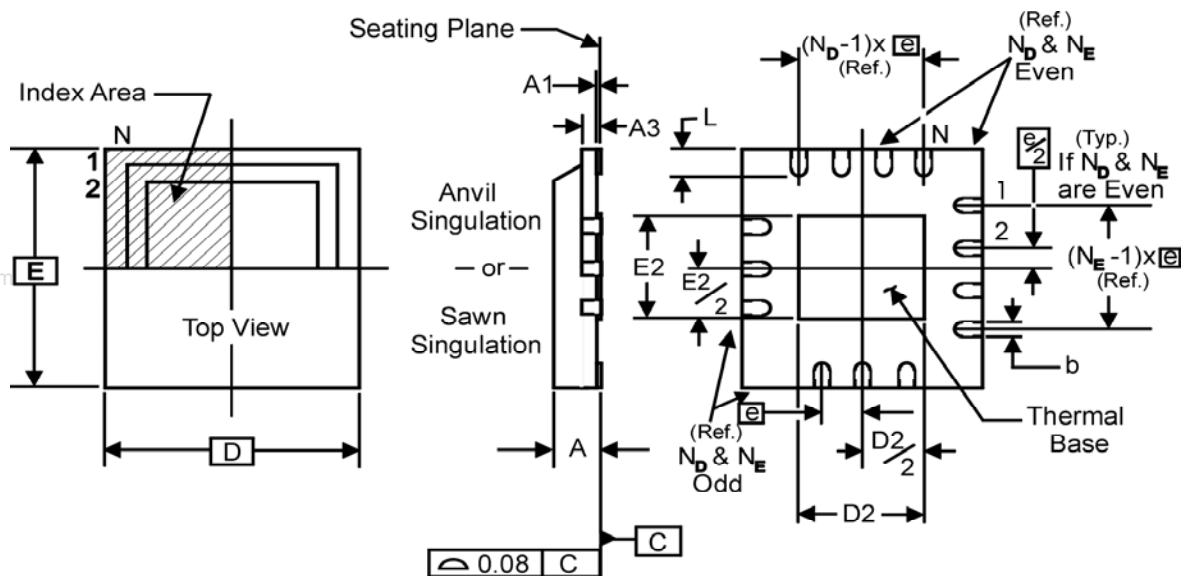


TABLE 8C. PACKAGE DIMENSIONS FOR 20 LEAD VFQFN

JEDEC VARIATION ALL DIMENSIONS IN MILLIMETERS		
SYMBOL	MINIMUM	MAXIMUM
N	20	
A	0.80	1.0
A1	0	0.05
A3	0.25 Reference	
b	0.18	0.30
e	0.50 BASIC	
N_D	5	
N_E	5	
D	4.0	
D2	0.75	2.80
E	4.0	
E2	0.75	2.80
L	0.35	0.75

Reference Document: JEDEC Publication 95, MO-220

TABLE 9. ORDERING INFORMATION

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
ICS83905AM	83905AM	16 Lead SOIC	tube	0°C to 70°C
ICS83905AMT	83905AM	16 Lead SOIC	2500 tape & reel	0°C to 70°C
ICS83905AML	83905AML	16 Lead "Lead-Free" SOIC	tube	0°C to 70°C
ICS83905AMLFT	83905AML	16 Lead "Lead-Free" SOIC	2500 tape & reel	0°C to 70°C
ICS83905AG	83905AG	16 Lead TSSOP	tube	0°C to 70°C
ICS83905AGT	83905AG	16 Lead TSSOP	2500 tape & reel	0°C to 70°C
ICS83905AGLF	83905AGL	16 Lead "Lead-Free" TSSOP	tube	0°C to 70°C
ICS83905AGLFT	83905AGL	16 Lead "Lead-Free" TSSOP	2500 tape & reel	0°C to 70°C
ICS83905AK	83905A	20 Lead VFQFN	tube	0°C to 70°C
ICS83905AKT	83905A	20 Lead VFQFN	2500 tape & reel	0°C to 70°C
ICS83905AKLF	3905AL	20 Lead "Lead-Free" VFQFN	tube	0°C to 70°C
ICS83905AKLFT	3905AL	20 Lead "Lead-Free" VFQFN	2500 tape & reel	0°C to 70°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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REVISION HISTORY SHEET

Rev	Table	Page	Description of Change	Date
A		2	Added Enable Timing Diagram.	3/28/05
B	6A - 6F	1 5 - 7 8	Features Section - added RMS Phase Jitter bullet. AC Characteristics Tables - added RMS Phase Jitter spec. Added Phase Noise Plot.	4/8/05
B	T9	14	Ordering Information Table - add TSSOP, non-LF part number.	4/25/05
B		11 12	Added Crystal Input Interface in Application Section. Added schematic layout.	5/16/05
B	T7C	3 11 13	Absolute Maximum Ratings - correct 20 lead VFQFN Package Thermal Impedance. Added <i>Recommendations for Unused Input and Output Pins</i> . Corrected Theta JA Air Flow Table for 20 lead VFQFN.	10/2/06
B	T9	11 12 17	Added <i>LVCMOS to XTAL Interface</i> section. Added <i>Thermal Release Path</i> section. AC Characteristics Table - added lead-free marking for 20 VFQFN package.	7/9/07

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